

**FOR IMMEDIATE RELEASE**  
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*For more information, contact:*  
**Christopher J. Rauh**  
**VP Sales & Marketing**  
**919-424-5181**  
[crauh@nitronex.com](mailto:crauh@nitronex.com)

**Kara Thompson**  
**Sales and Marketing Assistant**  
**919-424-5222**  
[kthompson@nitronex.com](mailto:kthompson@nitronex.com)

## **NITRONEX NAMES NEW DIRECTOR OF MARKETING**

Durham, N.C. (July 24, 2007) — Nitronex, an innovative developer and manufacturer of high-performance RF power transistors for the commercial and broadband wireless infrastructure markets, has named Ray Crampton as the new Director of Marketing. Mr. Crampton brings more than 10 years of industry experience spanning RF IC amplifier design, technical and marketing management to Nitronex.

"As the industry shifts to a new generation of high-efficiency, wide bandwidth power amplifiers using GaN transistors, the addition of Mr. Crampton enables us to accelerate our product definition and development activities. Ray will also lead our applications team which is a critical function in supporting our customers throughout the product life cycle," said Chris Rauh, VP Sales and Marketing at Nitronex.

Before joining Nitronex, Mr. Crampton served as a Strategic Marketing and Systems Engineering Manager for Texas Instruments' Linear Regulators product line. Prior to that, Mr. Crampton held various positions at Sirenza Microdevices including Product Line Manager, Engineering Manager and Senior RF IC Design Engineer. Mr. Crampton also served as RF IC Design Engineer and Engineering Manager at ITT GaAs TEK and Sr. RF IC Design Engineer at M/A-Com.

Mr. Crampton received his B.S.E.E. and M.S.E.E from Virginia Tech.

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For more information about GaN on Si manufacturing technology, contact Nitronex at 2305 Presidential Drive, Durham, NC 27703; call 919-807-9100; or e-mail [info@nitronex.com](mailto:info@nitronex.com).

### **About Nitronex**

Specializing in the development and manufacturing of gallium nitride (GaN) RF power devices, Nitronex is the global leader in high-performance GaN on silicon (GaN on Si) RF power transistors for the commercial wireless infrastructure, broadband and military markets. Based on its patented SIGANTIC<sup>®</sup> process — gallium nitride on silicon technology — Nitronex is at the forefront of commercializing GaN technology for RF applications. The company's ability to combine the disciplines of material growth, wafer processing, device design and wireless applications knowledge is unique to the industry.

Nitronex was founded in 1999 by graduates of the wide bandgap program at North Carolina State University and is headquartered in Durham, North Carolina. It holds 19 patents with 19 others pending.

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